# 512K x 8 Bit Static Random Access Memory

The MCM6246 is a 4,194,304 bit static random access memory organized as 524,288 words of 8 bits. Static design eliminates the need for external clocks or timing strobes, while CMOS circuitry reduces power consumption and provides for greater reliability.

The MCM6246 is equipped with chip enable (E) and output enable (G) pins, allowing for greater system flexibility and eliminating bus contention problems. Either input, when high, will force the outputs into high impedance.

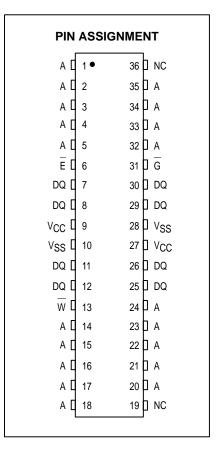
The MCM6246 is available in a 400 mil, 36-lead surface-mount SOJ package.

- Single 5 V ± 10% Power Supply
- Fast Access Time: 17/20/25/35 ns
- Equal Address and Chip Enable Access Time
- All Inputs and Outputs are TTL Compatible
- Three-State Outputs
- Power Operation: 205/200/185/170 mA Maximum, Active AC

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# MCM6246





PIN NAMES
A. Address Inputs   W Write Enable   G Output Enable   E Chip Enable   DQ Data Input/Output   NC No Connection   VCC + 5 V Power Supply   VSS Ground

REV 5 6/9/97



#### **TRUTH TABLE** (X = Don't Care)

Е	G	w	Mode	I/O Pin	Cycle	Current
Н	Х	Х	Not Selected	High–Z	_	I <sub>SB1</sub> , I <sub>SB2</sub>
L	Н	Н	Output Disabled	High–Z	_	ICCA
L	L	Н	Read	D <sub>out</sub>	Read	ICCA
L	Х	L	Write	High-Z	Write	ICCA

#### **ABSOLUTE MAXIMUM RATINGS** (See Note)

Rating	Symbol	Value	Unit
Power Supply Voltage Relative to VSS	VCC	- 0.5 to + 7.0	V
Voltage Relative to V <sub>SS</sub> for Any Pin Except V <sub>CC</sub>	V <sub>in</sub> , V <sub>out</sub>	- 0.5 to V <sub>CC</sub> + 0.5	V
Output Current (per I/O)	l <sub>out</sub>	± 20	mA
Power Dissipation	PD	1.0	W
Temperature Under Bias	T <sub>bias</sub>	- 10 to + 85	°C
Ambient Temperature	TA	0 to + 70	°C
Storage Temperature — Plastic	T <sub>stg</sub>	- 55 to + 150	°C

NOTE: Permanent device damage may occur if ABSOLUTE MAXIMUM RATINGS are exceeded. Functional operation should be restricted to RECOMMENDED OPERAT-ING CONDITIONS. Exposure to higher than recommended voltages for extended periods of time could affect device reliability.

This device contains circuitry to protect the inputs against damage due to high static voltages or electric fields; however, it is advised that normal precautions be taken to avoid application of any voltage higher than maximum rated voltages to these high impedance circuits.

This CMOS memory circuit has been designed to meet the dc and ac specifications shown in the tables, after thermal equilibrium has been established. The circuit is in a test socket or mounted on a printed circuit board and transverse air flow of at least 500 linear feet per minute is maintained.

#### DC OPERATING CONDITIONS AND CHARACTERISTICS

(V<sub>CC</sub> = 5.0 V  $\pm$  10%, T<sub>A</sub> = 0 to + 70°C, Unless Otherwise Noted)

#### RECOMMENDED OPERATING CONDITIONS

Parameter	Symbol	Min	Тур	Max	Unit
Supply Voltage (Operating Voltage Range)	Vcc	4.5	5.0	5.5	V
Input High Voltage	VIH	2.2	_	V <sub>CC</sub> + 0.3**	V
Input Low Voltage	V <sub>IL</sub>	- 0.5*	_	0.8	V

<sup>\*</sup>  $V_{IL}$  (min) = -0.5 V dc;  $V_{IL}$  (min) = -2.0 V ac (pulse width  $\leq 2.0$  ns).

#### **DC CHARACTERISTICS**

Parameter	Symbol	Min	Max	Unit
Input Leakage Current (All Inputs, V <sub>in</sub> = 0 to V <sub>CC</sub> )	l <sub>lkg(l)</sub>	_	± 1.0	μΑ
Output Leakage Current (E = V <sub>IH</sub> , V <sub>Out</sub> = 0 to V <sub>CC</sub> )	l <sub>lkg(O)</sub>	_	± 1.0	μΑ
Output Low Voltage (I <sub>OL</sub> = + 8.0 mA)	VOL	_	0.4	V
Output High Voltage (IOH = - 4.0 mA)	Vон	2.4	_	V

#### **POWER SUPPLY CURRENTS**

Paramete	r	Symbol	Min	Тур	Max	Unit
AC Active Supply Current (I <sub>Out</sub> = 0 mA, V <sub>CC</sub> = max)	MCM6246-17: $t_{AVAV}$ = 17 ns MCM6246-20: $t_{AVAV}$ = 20 ns MCM6246-25: $t_{AVAV}$ = 25 ns MCM6246-35: $t_{AVAV}$ = 35 ns	ICC	1111	— 185 170 155	205 200 185 170	mA
AC_Standby Current (V <sub>CC</sub> = max, E = V <sub>IH</sub> , No other restrictions on other inputs)	MCM6246-17: $t_{AVAV}$ = 17 ns MCM6246-20: $t_{AVAV}$ = 20 ns MCM6246-25: $t_{AVAV}$ = 25 ns MCM6246-35: $t_{AVAV}$ = 35 ns	I <sub>SB1</sub>		55 55 45 35	60 60 50 40	mA
CMOS Standby Current (E $\geq$ V <sub>CC</sub> - 0.2 V $\geq$ V <sub>CC</sub> - 0.2 V) (V <sub>CC</sub> = max, f = 0 MHz		I <sub>SB2</sub>	_	10	15	mA

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<sup>\*\*</sup>  $V_{IH}$  (max) =  $V_{CC}$  + 0.3  $V_{CC}$ ;  $V_{IH}$  (max) =  $V_{CC}$  + 2.0  $V_{CC}$  ac (pulse width  $\leq$  2.0 ns).

#### **CAPACITANCE** (f = 1.0 MHz, dV = 3.0 V, T<sub>A</sub> = 25°C, Periodically Sampled Rather Than 100% Tested)

	' ' ' ===				Unit
Input Capacitance	All Inputs Except Clocks a <u>nd DQs</u> E, G, W	C <sub>in</sub> C <sub>ck</sub>	4 5	6 8	pF
Input/Output Capacitance	DQ	C <sub>I/O</sub>	5	8	pF

#### **AC OPERATING CONDITIONS AND CHARACTERISTICS**

(V<sub>CC</sub> = 5.0 V  $\pm$  10%, T<sub>A</sub> = 0 to + 70°C, Unless Otherwise Noted)

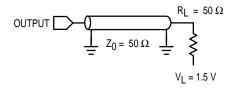
Input Pulse Levels 0 to 3.0 V	Output Timing Measurement Reference Level 1.5 V
Input Rise/Fall Time	Output Load See Figure 1
Input Timing Measurement Reference Level 1.5 V	

#### **READ CYCLE TIMING** (See Note 1)

		MCM6246-17		MCM6246-20 MCM6246-25			246–25	MCM6	246–35		
Parameter	Symbol	Min	Max	Min	Max	Min	Max	Min	Max	Unit	Notes
Read Cycle Time	tAVAV	17	_	20	_	25	_	35	_	ns	2, 3
Address Access Time	tAVQV	_	17	_	20	_	25	_	35	ns	
Enable Access Time	t <sub>ELQV</sub>	_	17	_	20	_	25	_	35	ns	4
Output Enable Access Time	tGLQV	_	6	_	6	_	8	_	10	ns	
Output Hold from Address Change	tAXQX	5	_	5	_	5	_	5	_	ns	
Enable Low to Output Active	tELQX	5	_	5	_	5	_	5	_	ns	5, 6, 7
Output Enable Low to Output Active	<sup>t</sup> GLQX	0	_	0	_	0	_	0	_	ns	5, 6, 7
Enable High to Output High–Z	tEHQZ	_	8	_	8	_	10	_	12	ns	5, 6, 7
Output Enable High to Output High–Z	<sup>t</sup> GHQZ	_	8	_	8	_	10	_	12	ns	5, 6, 7
Power Up Time	tELICCH	0	_	0	_	0	_	0	_	ns	
Power Down Time	<sup>t</sup> EHICCL	_	17	_	20	_	25	_	35	ns	

#### NOTES:

- 1. W is high for read cycle.
- 2. Product sensitivities to noise require proper grounding and decoupling of power supplies as well as minimization or elimination of bus contention conditions during read and write cycles.
- 3. All read cycle timings are referenced from the last valid address to the first transitioning address.
- 4. Addresses valid prior to or coincident with E going low/E going high.
- 5. At any given voltage and temperature, tehQZ max < telQX min, and tghQZ max < tglQX min, both for a given device and from device to device.
- 6. Transition is measured  $\pm$  500 mV from steady–state voltage.
- 7. This parameter is sampled and not 100% tested.
- 8. Device is continuously selected (E  $\leq$  V<sub>IL</sub>, G  $\leq$  V<sub>IL</sub>).



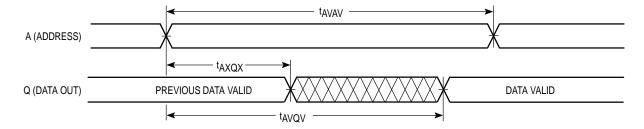
#### **TIMING LIMITS**

The table of timing values shows either a minimum or a maximum limit for each parameter. Input requirements are specified from the external system point of view. Thus, address setup time is shown as a minimum since the system must supply at least that much time. On the other hand, responses from the memory are specified from the device point of view. Thus, the access time is shown as a maximum since the device never provides data later than that time.

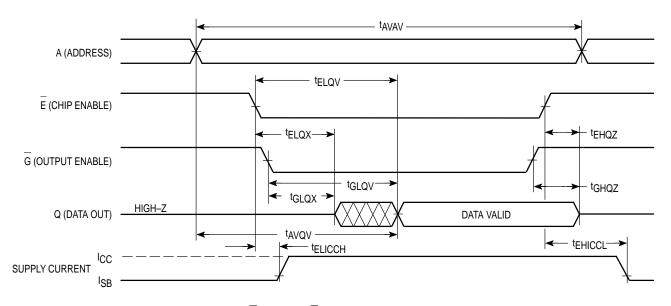
Figure 1. AC Test Load

MOTOROLA FAST SRAM MCM6246

### READ CYCLE 1 (See Note 8)



### READ CYCLE 2 (See Note)



NOTE: Addresses valid prior to or coincident with  $\overline{E}$  going low/  $\overline{E}$  going high.

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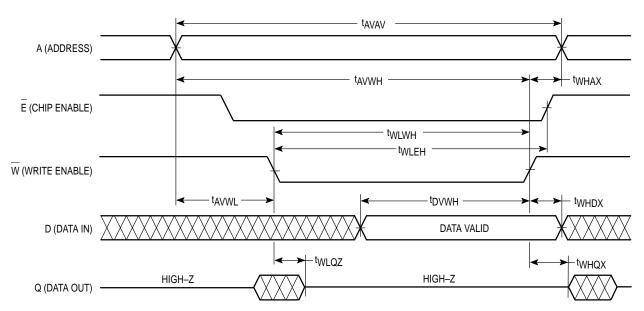
WRITE CYCLE 1 (W Controlled, See Notes 1, 2, and 3)

		MCM6246-17		MCM6	MCM6246-20		MCM6246-25		5 MCM6246-35		
Parameter	Symbol	Min	Max	Min	Max	Min	Max	Min	Max	Unit	Notes
Write Cycle Time	tAVAV	17	_	20	_	25	_	35	_	ns	4
Address Setup Time	†AVWL	0	_	0	_	0	_	0	_	ns	
Address Valid to End of Write	<sup>t</sup> AVWH	14	_	14	_	17	_	20	_	ns	
Write Pulse Width	tWLWH, tWLEH	13	_	13	_	17	_	20	_	ns	
Data Valid to End of Write	<sup>t</sup> DVWH	10	_	10	_	10	_	15	_	ns	
Data Hold Time	tWHDX	0	_	0	_	0	_	0	_	ns	
Write Low to Data High–Z	tWLQZ	0	9	0	9	0	10	0	15	ns	5,6,7
Write High to Output Active	tWHQX	5	_	5	_	5	_	5	_	ns	5,6,7
Write Recovery Time	tWHAX	0	_	0	_	0	_	0	_	ns	

#### NOTES:

- 1. A write occurs during the overlap of E low and  $\overline{W}$  low.
- 2. Product sensitivities to noise require proper grounding and decoupling of power supplies as well as minimization or elimination of bus contention conditions during read and write cycles.
- 3. If G goes low coincident with or after W goes low, the output will remain in a high-impedance state.
- 4. All write cycle timings are referenced from the last valid address to the first transitioning address.
- 5. Transition is measured  $\pm$  500 mV from steady–state voltage.
- 6. This parameter is sampled and not 100% tested.
- 7. At any given voltage and temperature, tWLQZ max < tWHQX min both for a given device and from device to device.

# WRITE CYCLE 1 (W Controlled, See Notes 1, 2, and 3)



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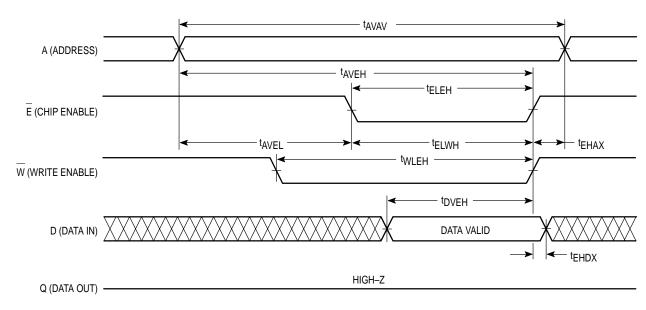
WRITE CYCLE 2 (E Controlled, See Notes 1, 2, and 3)

		мсм6	MCM6246-17		MCM6246-20		MCM6246-25		MCM6246-35		
Parameter	Symbol	Min	Max	Min	Max	Min	Max	Min	Max	Unit	Notes
Write Cycle Time	tAVAV	17	_	20	_	25	_	35	_	ns	4
Address Setup Time	<sup>t</sup> AVEL	0	_	0	_	0	_	0	_	ns	
Address Valid to End of Write	<sup>t</sup> AVEH	14	_	14	_	17	_	20	_	ns	
Enable Pulse Width	tELEH, tELWH	14	_	14	_	17	_	20	_	ns	5,6
Write Pulse Width	tWLEH	14	_	14	_	17	_	20	_	ns	
Data Valid to End of Write	<sup>t</sup> DVEH	9	_	10	_	10	_	15	_	ns	
Data Hold Time	tEHDX	0	_	0	_	0	_	0	_	ns	
Write Recovery Time	tEHAX	0	_	0	_	0	_	0	_	ns	

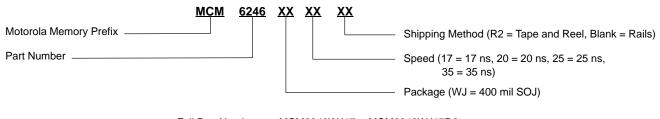
#### NOTES:

- 1. A write occurs during the overlap of E low and W low.
- 2. Product sensitivities to noise require proper grounding and decoupling of power supplies as well as minimization or elimination of bus contention conditions during read and write cycles.
- 3. If G goes low coincident with or after W goes low, the output will remain in a high-impedance state.
- 4. All write cycle timing is referenced from the last valid address to the first transitioning address.
- 5. If <u>E</u> goes low coincident with or after W goes low, the output will remain in a high impedance condition.
- 6. If E goes high coincident with or before W goes high, the output will remain in a high impedance condition.

## WRITE CYCLE 2 (E Controlled, See Notes 1, 2, and 3)



# ORDERING INFORMATION (Order by Full Part Number)

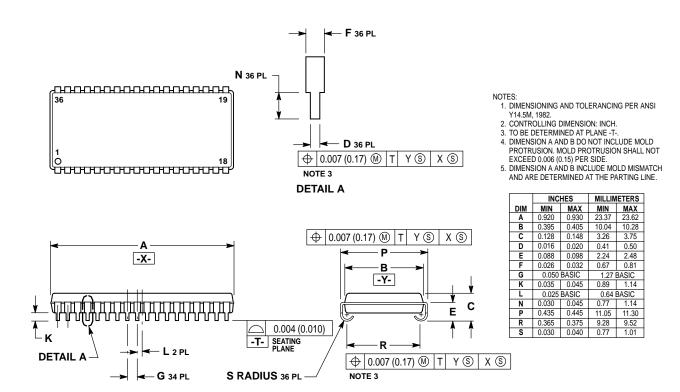


Full Part Numbers — MCM6246WJ17 MCM6246WJ17R2

MCM6246WJ20 MCM6246WJ20R2 MCM6246WJ25 MCM6246WJ25R2 MCM6246WJ35 MCM6246WJ35R2

#### **PACKAGE DIMENSIONS**

#### 400 MIL SOJ CASE 893-01



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